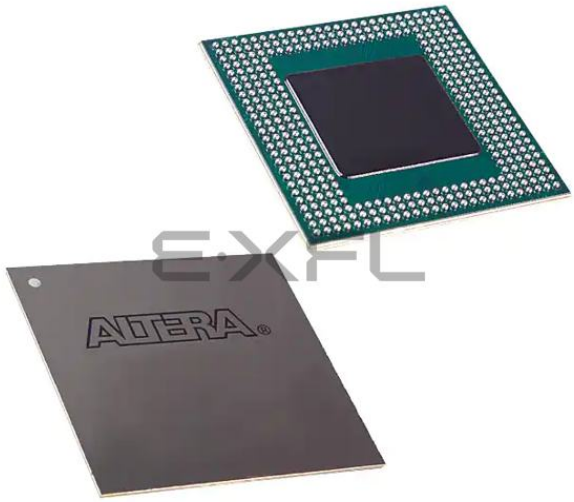

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	360
Number of Logic Elements/Cells	2880
Total RAM Bits	20480
Number of I/O	274
Number of Gates	116000
Voltage - Supply	3V ~ 3.6V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	356-LBGA
Supplier Device Package	356-BGA (35x35)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epf10k50vbc356-2

Table 2. FLEX 10K Device Features

Feature	EPF10K70	EPF10K100 EPF10K100A	EPF10K130V	EPF10K250A
Typical gates (logic and RAM) *(1)*	70,000	100,000	130,000	250,000
Maximum system gates	118,000	158,000	211,000	310,000
LEs	3,744	4,992	6,656	12,160
LABs	468	624	832	1,520
EABs	9	12	16	20
Total RAM bits	18,432	24,576	32,768	40,960
Maximum user I/O pins	358	406	470	470

Note to tables:

(1) The embedded IEEE Std. 1149.1 JTAG circuitry adds up to 31,250 gates in addition to the listed typical or maximum system gates.

...and More Features

- Devices are fabricated on advanced processes and operate with a 3.3-V or 5.0-V supply voltage (see Table 3
- In-circuit reconfigurability (ICR) via external configuration device, intelligent controller, or JTAG port
- ClockLock™ and ClockBoost™ options for reduced clock delay/skew and clock multiplication
- Built-in low-skew clock distribution trees
- 100% functional testing of all devices; test vectors or scan chains are not required

Table 3. Supply Voltages for FLEX 10K & FLEX 10KA Devices

5.0-V Devices	3.3-V Devices
EPF10K10 EPF10K20 EPF10K30 EPF10K40 EPF10K50 EPF10K70 EPF10K100	EPF10K10A EPF10K30A EPF10K50V EPF10K100A EPF10K130V EPF10K250A

The FLEX 10K architecture is similar to that of embedded gate arrays, the fastest-growing segment of the gate array market. As with standard gate arrays, embedded gate arrays implement general logic in a conventional "sea-of-gates" architecture. In addition, embedded gate arrays have dedicated die areas for implementing large, specialized functions. By embedding functions in silicon, embedded gate arrays provide reduced die area and increased speed compared to standard gate arrays. However, embedded megafunctions typically cannot be customized, limiting the designer's options. In contrast, FLEX 10K devices are programmable, providing the designer with full control over embedded megafunctions and general logic while facilitating iterative design changes during debugging.

Each FLEX 10K device contains an embedded array and a logic array. The embedded array is used to implement a variety of memory functions or complex logic functions, such as digital signal processing (DSP), microcontroller, wide-data-path manipulation, and data-transformation functions. The logic array performs the same function as the sea-of-gates in the gate array: it is used to implement general logic, such as counters, adders, state machines, and multiplexers. The combination of embedded and logic arrays provides the high performance and high density of embedded gate arrays, enabling designers to implement an entire system on a single device.

FLEX 10K devices are configured at system power-up with data stored in an Altera serial configuration device or provided by a system controller. Altera offers the EPC1, EPC2, EPC16, and EPC1441 configuration devices, which configure FLEX 10K devices via a serial data stream. Configuration data can also be downloaded from system RAM or from Altera's BitBlaster™ serial download cable or ByteBlasterMV™ parallel port download cable. After a FLEX 10K device has been configured, it can be reconfigured in-circuit by resetting the device and loading new data. Because reconfiguration requires less than 320 ms, real-time changes can be made during system operation.

FLEX 10K devices contain an optimized interface that permits microprocessors to configure FLEX 10K devices serially or in parallel, and synchronously or asynchronously. The interface also enables microprocessors to treat a FLEX 10K device as memory and configure the device by writing to a virtual memory location, making it very easy for the designer to reconfigure the device.

The logic array consists of logic array blocks (LABs). Each LAB contains eight LEs and a local interconnect. An LE consists of a 4-input look-up table (LUT), a programmable flipflop, and dedicated signal paths for carry and cascade functions. The eight LEs can be used to create medium-sized blocks of logic—8-bit counters, address decoders, or state machines—or combined across LABs to create larger logic blocks. Each LAB represents about 96 usable gates of logic.

Signal interconnections within FLEX 10K devices and to and from device pins are provided by the FastTrack Interconnect, a series of fast, continuous row and column channels that run the entire length and width of the device.

Each I/O pin is fed by an I/O element (IOE) located at the end of each row and column of the FastTrack Interconnect. Each IOE contains a bidirectional I/O buffer and a flipflop that can be used as either an output or input register to feed input, output, or bidirectional signals. When used with a dedicated clock pin, these registers provide exceptional performance. As inputs, they provide setup times as low as 1.6 ns and hold times of 0 ns; as outputs, these registers provide clock-to-output times as low as 5.3 ns. IOEs provide a variety of features, such as JTAG BST support, slew-rate control, tri-state buffers, and open-drain outputs.

Figure 1 shows a block diagram of the FLEX 10K architecture. Each group of LEs is combined into an LAB; LABs are arranged into rows and columns. Each row also contains a single EAB. The LABs and EABs are interconnected by the FastTrack Interconnect. IOEs are located at the end of each row and column of the FastTrack Interconnect.

Logic functions are implemented by programming the EAB with a read-only pattern during configuration, creating a large LUT. With LUTs, combinatorial functions are implemented by looking up the results, rather than by computing them. This implementation of combinatorial functions can be faster than using algorithms implemented in general logic, a performance advantage that is further enhanced by the fast access times of EABs. The large capacity of EABs enables designers to implement complex functions in one logic level without the routing delays associated with linked LEs or field-programmable gate array (FPGA) RAM blocks. For example, a single EAB can implement a 4 × 4 multiplier with eight inputs and eight outputs. Parameterized functions such as LPM functions can automatically take advantage of the EAB.

The EAB provides advantages over FPGAs, which implement on-board RAM as arrays of small, distributed RAM blocks. These FPGA RAM blocks contain delays that are less predictable as the size of the RAM increases. In addition, FPGA RAM blocks are prone to routing problems because small blocks of RAM must be connected together to make larger blocks. In contrast, EABs can be used to implement large, dedicated blocks of RAM that eliminate these timing and routing concerns.

EABs can be used to implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable (WE) signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the WE signal. In contrast, the EAB's synchronous RAM generates its own WE signal and is self-timed with respect to the global clock. A circuit using the EAB's self-timed RAM need only meet the setup and hold time specifications of the global clock.

When used as RAM, each EAB can be configured in any of the following sizes: 256 × 8, 512 × 4, 1,024 × 2, or 2,048 × 1. See Figure 2.

Figure 2. EAB Memory Configurations

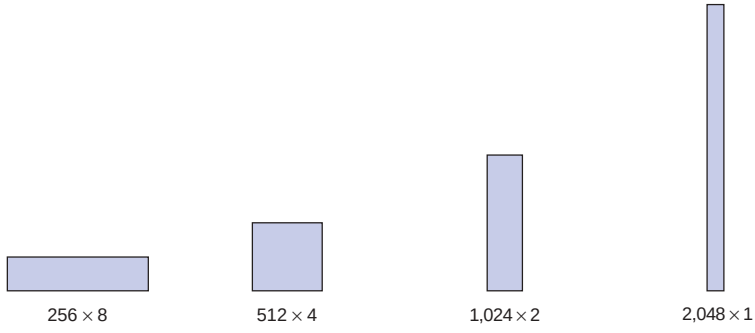
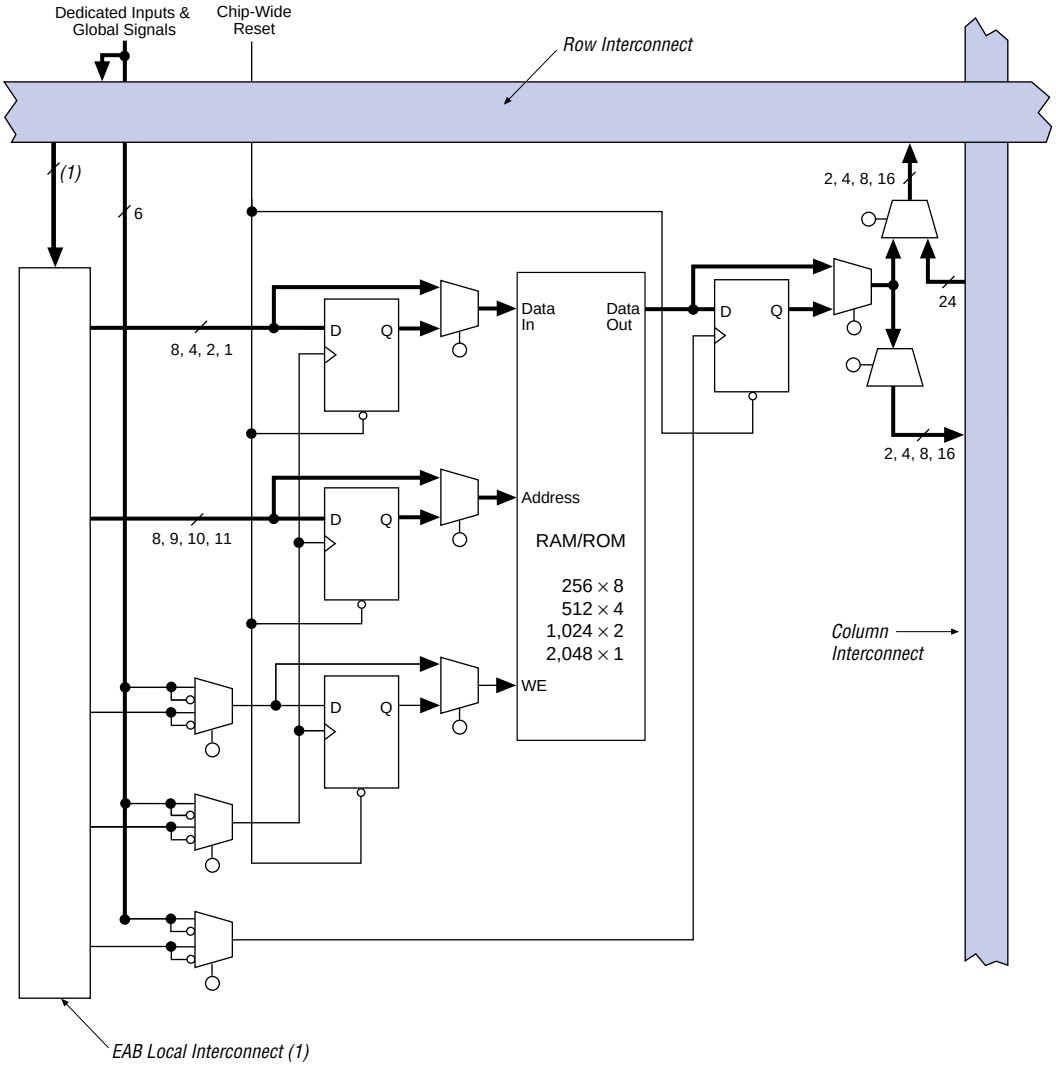


Figure 4. FLEX 10K Embedded Array Block



Note:

(1) EPF10K10, EPF10K10A, EPF10K20, EPF10K30, EPF10K30A, EPF10K40, EPF10K50, and EPF10K50V devices have 22 EAB local interconnect channels; EPF10K70, EPF10K100, EPF10K100A, EPF10K130V, and EPF10K250A devices have 26.

Each LAB provides four control signals with programmable inversion that can be used in all eight LEs. Two of these signals can be used as clocks; the other two can be used for clear/preset control. The LAB clocks can be driven by the dedicated clock input pins, global signals, I/O signals, or internal signals via the LAB local interconnect. The LAB preset and clear control signals can be driven by the global signals, I/O signals, or internal signals via the LAB local interconnect. The global control signals are typically used for global clock, clear, or preset signals because they provide asynchronous control with very low skew across the device. If logic is required on a control signal, it can be generated in one or more LEs in any LAB and driven into the local interconnect of the target LAB. In addition, the global control signals can be generated from LE outputs.

Logic Element

The LE, the smallest unit of logic in the FLEX 10K architecture, has a compact size that provides efficient logic utilization. Each LE contains a four-input LUT, which is a function generator that can quickly compute any function of four variables. In addition, each LE contains a programmable flipflop with a synchronous enable, a carry chain, and a cascade chain. Each LE drives both the local and the FastTrack Interconnect. See Figure 6.

Figure 6. FLEX 10K Logic Element

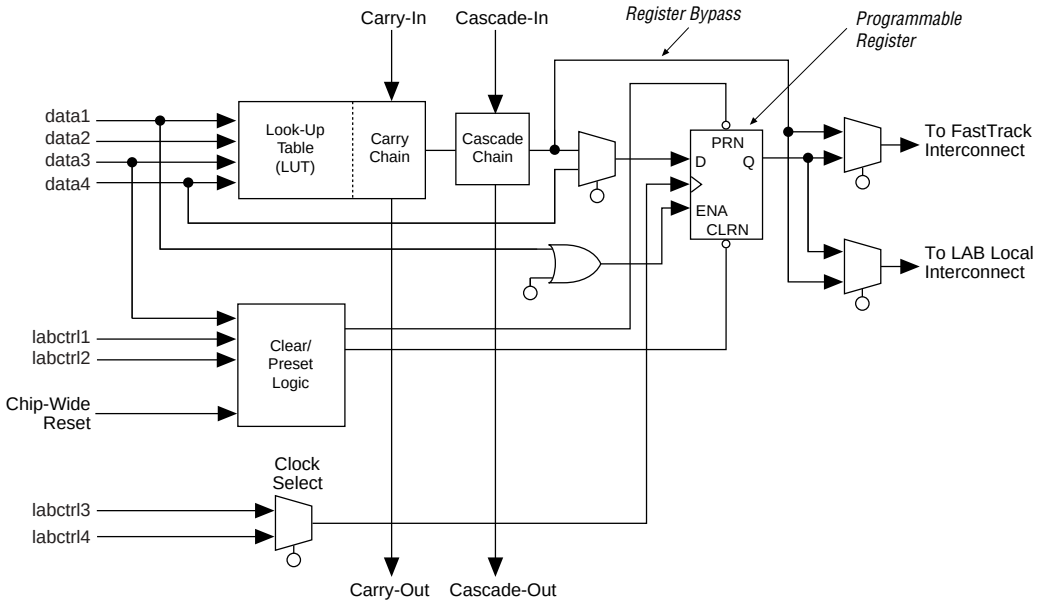
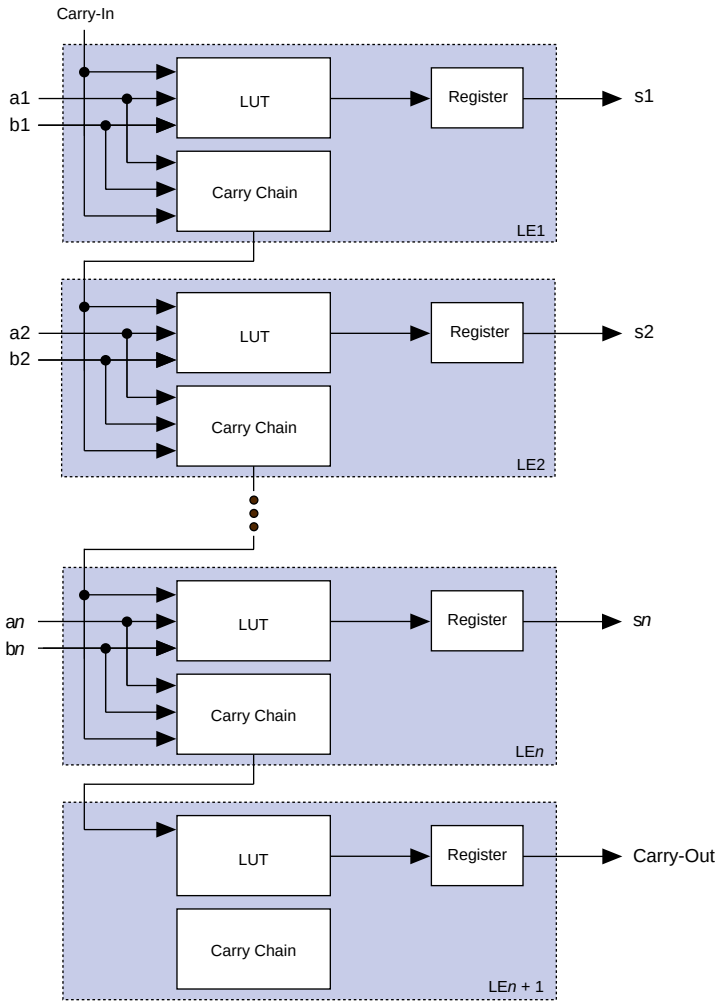


Figure 7 shows how an *n*-bit full adder can be implemented in *n* + 1 LEs with the carry chain. One portion of the LUT generates the sum of two bits using the input signals and the carry-in signal; the sum is routed to the output of the LE. The register can either be bypassed for simple adders or be used for an accumulator function. The carry chain logic generates the carry-out signal, which is routed directly to the carry-in signal of the next-higher-order bit. The final carry-out signal is routed to an LE, where it can be used as a general-purpose signal.

Figure 7. Carry Chain Operation (n-bit Full Adder)



Cascade Chain

With the cascade chain, the FLEX 10K architecture can implement functions that have a very wide fan-in. Adjacent LUTs can be used to compute portions of the function in parallel; the cascade chain serially connects the intermediate values. The cascade chain can use a logical AND or logical OR (via De Morgan's inversion) to connect the outputs of adjacent LEs. Each additional LE provides four more inputs to the effective width of a function, with a delay as low as 0.7 ns per LE. Cascade chain logic can be created automatically by the Compiler during design processing, or manually by the designer during design entry.

Cascade chains longer than eight bits are implemented automatically by linking several LABs together. For easier routing, a long cascade chain skips every other LAB in a row. A cascade chain longer than one LAB skips either from even-numbered LAB to even-numbered LAB, or from odd-numbered LAB to odd-numbered LAB (e.g., the last LE of the first LAB in a row cascades to the first LE of the third LAB). The cascade chain does not cross the center of the row (e.g., in the EPF10K50 device, the cascade chain stops at the eighteenth LAB and a new one begins at the nineteenth LAB). This break is due to the EAB's placement in the middle of the row.

Figure 8 shows how the cascade function can connect adjacent LEs to form functions with a wide fan-in. These examples show functions of 4*n* variables implemented with *n* LEs. The LE delay is as low as 1.6 ns; the cascade chain delay is as low as 0.7 ns. With the cascade chain, 3.7 ns is needed to decode a 16-bit address.

Figure 8. Cascade Chain Operation

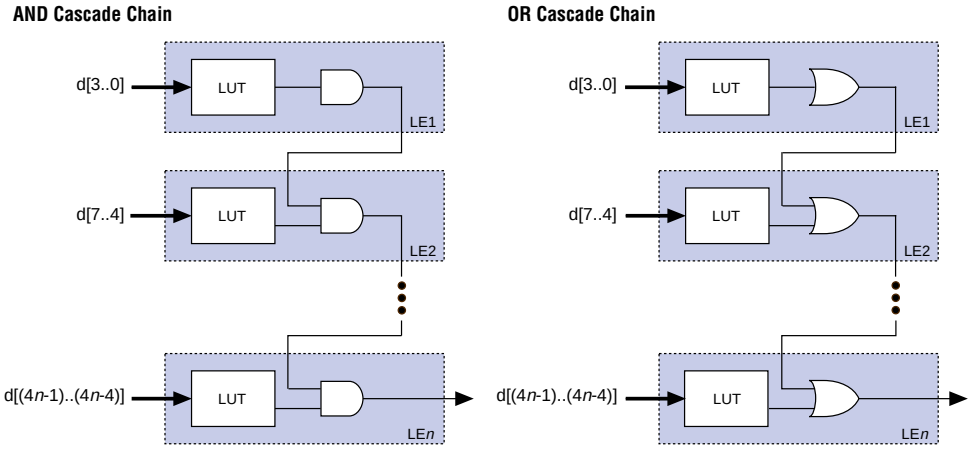
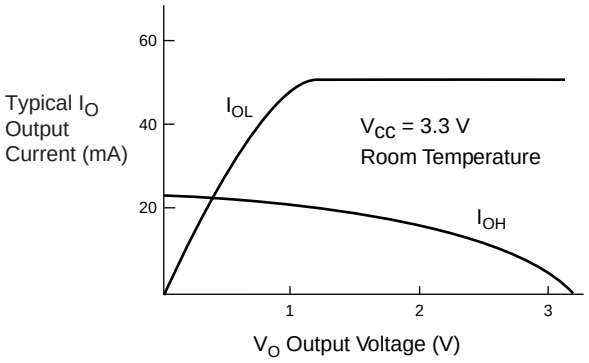


Figure 21 shows the typical output drive characteristics of EPF10K50V and EPF10K130V devices.

Figure 21. Output Drive Characteristics of EPF10K50V & EPF10K130V Devices



Tables 26 through 31 provide information on absolute maximum ratings, recommended operating conditions, DC operating conditions, and capacitance for 3.3-V FLEX 10K devices.

Table 26. FLEX 10KA 3.3-V Device Absolute Maximum Ratings *Note (1)*

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	Supply voltage	With respect to ground *(2)*	–0.5	4.6	V
V_I	DC input voltage		–2.0	5.75	V
I_{OUT}	DC output current, per pin		–25	25	mA
T_{STG}	Storage temperature	No bias	–65	150	° C
T_{AMB}	Ambient temperature	Under bias	–65	135	° C
T_J	Junction temperature	Ceramic packages, under bias		150	° C
		PQFP, TQFP, RQFP, and BGA packages, under bias		135	° C

Table 28. FLEX 10KA 3.3-V Device DC Operating Conditions *Notes (6), (7)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IH}	High-level input voltage		1.7 or $0.5 \times V_{CCINT}$, whichever is lower		5.75	V
V_{IL}	Low-level input voltage		–0.5		$0.3 \times V_{CCINT}$	V
V_{OH}	3.3-V high-level TTL output voltage	I_{OH} = –11 mA DC, V_{CCIO} = 3.00 V *(8)*	2.4			V
	3.3-V high-level CMOS output voltage	I_{OH} = –0.1 mA DC, V_{CCIO} = 3.00 V *(8)*	V_{CCIO} – 0.2			V
	3.3-V high-level PCI output voltage	I_{OH} = –0.5 mA DC, V_{CCIO} = 3.00 to 3.60 V *(8)*	$0.9 \times V_{CCIO}$			V
	2.5-V high-level output voltage	I_{OH} = –0.1 mA DC, V_{CCIO} = 2.30 V *(8)*	2.1			V
		I_{OH} = –1 mA DC, V_{CCIO} = 2.30 V *(8)*	2.0			V
		I_{OH} = –2 mA DC, V_{CCIO} = 2.30 V *(8)*	1.7			V
V_{OL}	3.3-V low-level TTL output voltage	I_{OL} = 9 mA DC, V_{CCIO} = 3.00 V *(9)*			0.45	V
	3.3-V low-level CMOS output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 3.00 V *(9)*			0.2	V
	3.3-V low-level PCI output voltage	I_{OL} = 1.5 mA DC, V_{CCIO} = 3.00 to 3.60 V *(9)*			$0.1 \times V_{CCIO}$	V
	2.5-V low-level output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 2.30 V *(9)*			0.2	V
		I_{OL} = 1 mA DC, V_{CCIO} = 2.30 V *(9)*			0.4	V
		I_{OL} = 2 mA DC, V_{CCIO} = 2.30 V *(9)*			0.7	V
I_I	Input pin leakage current	V_I = 5.3 V to –0.3 V *(10)*	–10		10	µA
I_{OZ}	Tri-stated I/O pin leakage current	V_O = 5.3 V to –0.3 V *(10)*	–10		10	µA
I_{CC0}	V_{CC} supply current (standby)	V_I = ground, no load		0.3	10	mA
		V_I = ground, no load *(11)*		10		mA

Table 29. 3.3-V Device Capacitance of EPF10K10A & EPF10K30A Devices *Note (12)*

Symbol	Parameter	Conditions	Min	Max	Unit
C_{IN}	Input capacitance	V_{IN} = 0 V, f = 1.0 MHz		8	pF
C_{INCLK}	Input capacitance on dedicated clock pin	V_{IN} = 0 V, f = 1.0 MHz		12	pF
C_{OUT}	Output capacitance	V_{OUT} = 0 V, f = 1.0 MHz		8	pF

Table 30. 3.3-V Device Capacitance of EPF10K100A Devices *Note (12)*

Symbol	Parameter	Conditions	Min	Max	Unit
C_{IN}	Input capacitance	V_{IN} = 0 V, f = 1.0 MHz		10	pF
C_{INCLK}	Input capacitance on dedicated clock pin	V_{IN} = 0 V, f = 1.0 MHz		15	pF
C_{OUT}	Output capacitance	V_{OUT} = 0 V, f = 1.0 MHz		10	pF

Table 31. 3.3-V Device Capacitance of EPF10K250A Devices *Note (12)*

Symbol	Parameter	Conditions	Min	Max	Unit
C_{IN}	Input capacitance	V_{IN} = 0 V, f = 1.0 MHz		10	pF
C_{INCLK}	Input capacitance on dedicated clock pin	V_{IN} = 0 V, f = 1.0 MHz		15	pF
C_{OUT}	Output capacitance	V_{OUT} = 0 V, f = 1.0 MHz		10	pF

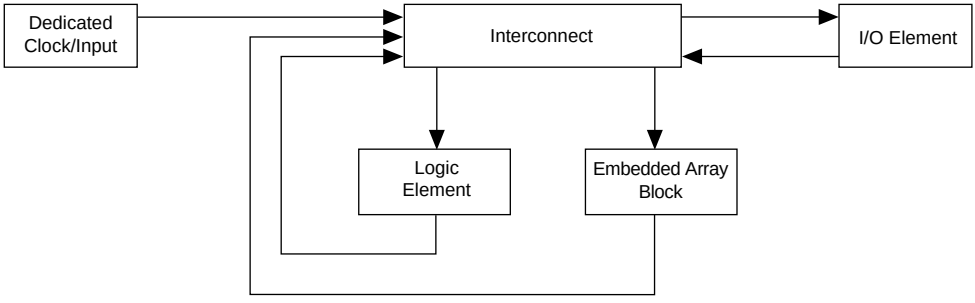
Notes to tables:

(1) See the *Operating Requirements for Altera Devices Data Sheet*.
(2) Minimum DC voltage input is –0.5 V. During transitions, the inputs may undershoot to –2.0 V or overshoot to 5.75 V for input currents less than 100 mA and periods shorter than 20 ns.
(3) Numbers in parentheses are for industrial-temperature-range devices.
(4) Maximum V_{CC} rise time is 100 ms, and V_{CC} must rise monotonically.
(5) FLEX 10KA device inputs may be driven before V_{CCINT} and V_{CCIO} are powered.
(6) Typical values are for T_A = 25° C and V_{CC} = 3.3 V.
(7) These values are specified under the Recommended Operating Conditions shown in Table 27 on page 51.
(8) The I_{OH} parameter refers to high-level TTL, PCI, or CMOS output current.
(9) The I_{OL} parameter refers to low-level TTL, PCI, or CMOS output current. This parameter applies to open-drain pins as well as output pins.
(10) This value is specified for normal device operation. The value may vary during power-up.
(11) This parameter applies to all -1 speed grade commercial temperature devices and all -2 speed grade industrial-temperature devices.
(12) Capacitance is sample-tested only.

Timing simulation and delay prediction are available with the MAX+PLUS II Simulator and Timing Analyzer, or with industry-standard EDA tools. The Simulator offers both pre-synthesis functional simulation to evaluate logic design accuracy and post-synthesis timing simulation with 0.1-ns resolution. The Timing Analyzer provides point-to-point timing delay information, setup and hold time analysis, and device-wide performance analysis.

Figure 24 shows the overall timing model, which maps the possible paths to and from the various elements of the FLEX 10K device.

Figure 24. FLEX 10K Device Timing Model



Notes to tables:

(1) Microparameters are timing delays contributed by individual architectural elements. These parameters cannot be measured explicitly.

(2) Operating conditions: V_{CCIO} = 5.0 V ± 5% for commercial use in FLEX 10K devices.
V_{CCIO} = 5.0 V ± 10% for industrial use in FLEX 10K devices.
V_{CCIO} = 3.3 V ± 10% for commercial or industrial use in FLEX 10KA devices.

(3) Operating conditions: V_{CCIO} = 3.3 V ± 10% for commercial or industrial use in FLEX 10K devices.
V_{CCIO} = 2.5 V ± 0.2 V for commercial or industrial use in FLEX 10KA devices.

(4) Operating conditions: V_{CCIO} = 2.5 V, 3.3 V, or 5.0 V.

(5) Because the RAM in the EAB is self-timed, this parameter can be ignored when the WE signal is registered.

(6) EAB macroparameters are internal parameters that can simplify predicting the behavior of an EAB at its boundary; these parameters are calculated by summing selected microparameters.

(7) These parameters are worst-case values for typical applications. Post-compilation timing simulation and timing analysis are required to determine actual worst-case performance.

(8) External reference timing parameters are factory-tested, worst-case values specified by Altera. A representative subset of signal paths is tested to approximate typical device applications.

(9) Contact Altera Applications for test circuit specifications and test conditions.

(10) These timing parameters are sample-tested only.

Figures 29 and 30 show the asynchronous and synchronous timing waveforms, respectively, for the EAB macroparameters in Table 34.

Figure 29. EAB Asynchronous Timing Waveforms

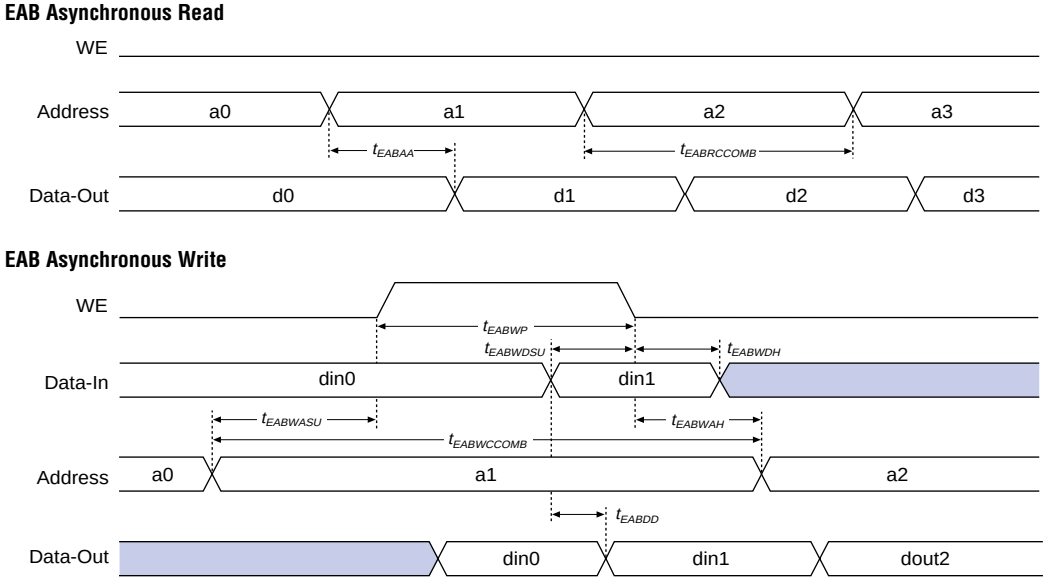


Table 45. EPF10K10 & EPF10K20 Device External Timing Parameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
t_{DRR}		16.1		20.0	ns
t_{INSU} *(2)*, *(3)*	5.5		6.0		ns
t_{INH} *(3)*	0.0		0.0		ns
t_{OUTCO} *(3)*	2.0	6.7	2.0	8.4	ns

Table 46. EPF10K10 Device External Bidirectional Timing Parameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
$t_{INSUBIDIR}$	4.5		5.6		ns
$t_{INHBIDIR}$	0.0		0.0		ns
$t_{OUTCOBIDIR}$	2.0	6.7	2.0	8.4	ns
$t_{XZBIDIR}$		10.5		13.4	ns
$t_{ZXBIDIR}$		10.5		13.4	ns

Table 47. EPF10K20 Device External Bidirectional Timing Parameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
$t_{INSUBIDIR}$	4.6		5.7		ns
$t_{INHBIDIR}$	0.0		0.0		ns
$t_{OUTCOBIDIR}$	2.0	6.7	2.0	8.4	ns
$t_{XZBIDIR}$		10.5		13.4	ns
$t_{ZXBIDIR}$		10.5		13.4	ns

Notes to tables:

(1) All timing parameters are described in Tables 32 through 38 in this data sheet.
(2) Using an LE to register the signal may provide a lower setup time.
(3) This parameter is specified by characterization.

Table 65. EPF10K100 Device IOE Timing Microparameters *Note (1)*

Symbol	-3DX Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{IOD}		0.0		0.0		0.0	ns
t_{IOC}		0.5		0.5		0.7	ns
t_{IOCO}		0.4		0.4		0.9	ns
t_{IOCOMB}		0.0		0.0		0.0	ns
t_{IOSU}	5.5		5.5		6.7		ns
t_{IOH}	0.5		0.5		0.7		ns
t_{IOCLR}		0.7		0.7		1.6	ns
t_{OD1}		4.0		4.0		5.0	ns
t_{OD2}		6.3		6.3		7.3	ns
t_{OD3}		7.7		7.7		8.7	ns
t_{XZ}		6.2		6.2		6.8	ns
t_{ZX1}		6.2		6.2		6.8	ns
t_{ZX2}		8.5		8.5		9.1	ns
t_{ZX3}		9.9		9.9		10.5	ns
t_{INREG} without ClockLock or ClockBoost circuitry		9.0		9.0		10.5	ns
t_{INREG} with ClockLock or ClockBoost circuitry		3.0		–		–	ns
t_{IOFD}		8.1		8.1		10.3	ns
t_{INCOMB}		8.1		8.1		10.3	ns

Table 66. EPF10K100 Device EAB Internal Microparameters *Note (1)*

Symbol	-3DX Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		1.5		1.5		1.9	ns
$t_{EABDATA2}$		4.8		4.8		6.0	ns
t_{EABWE1}		1.0		1.0		1.2	ns
t_{EABWE2}		5.0		5.0		6.2	ns
t_{EABCLK}		1.0		1.0		2.2	ns
t_{EABCO}		0.5		0.5		0.6	ns
$t_{EABBYPASS}$		1.5		1.5		1.9	ns
t_{EABSU}	1.5		1.5		1.8		ns
t_{EABH}	2.0		2.0		2.5		ns
t_{AA}		8.7		8.7		10.7	ns
t_{WP}	5.8		5.8		7.2		ns
t_{WDSU}	1.6		1.6		2.0		ns
t_{WDH}	0.3		0.3		0.4		ns
t_{WASU}	0.5		0.5		0.6		ns
t_{WAH}	1.0		1.0		1.2		ns
t_{WO}		5.0		5.0		6.2	ns
t_{DD}		5.0		5.0		6.2	ns
t_{EABOUT}		0.5		0.5		0.6	ns
t_{EABCH}	4.0		4.0		4.0		ns
t_{EABCL}	5.8		5.8		7.2		ns

Table 67. EPF10K100 Device EAB Internal Timing Macroparameters *Note (1)*

Symbol	-3DX Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{EABAA}		13.7		13.7		17.0	ns
$t_{EABRCCOMB}$	13.7		13.7		17.0		ns
$t_{EABRCREG}$	9.7		9.7		11.9		ns
t_{EABWP}	5.8		5.8		7.2		ns
$t_{EABWCCOMB}$	7.3		7.3		9.0		ns
$t_{EABWCREG}$	13.0		13.0		16.0		ns
t_{EABDD}		10.0		10.0		12.5	ns
$t_{EABDATACO}$		2.0		2.0		3.4	ns
$t_{EABDATASU}$	5.3		5.3		5.6		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	5.5		5.5		5.8		ns
t_{EABWEH}	0.0		0.0		0.0		ns
$t_{EABWDSU}$	5.5		5.5		5.8		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	2.1		2.1		2.7		ns
t_{EABWAH}	0.0		0.0		0.0		ns
t_{EABWO}		9.5		9.5		11.8	ns

Table 73. EPF10K50V Device EAB Internal Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		1.7		2.8		3.4		4.6	ns
$t_{EABDATA2}$		4.9		3.9		4.8		5.9	ns
t_{EABWE1}		0.0		2.5		3.0		3.7	ns
t_{EABWE2}		4.0		4.1		5.0		6.2	ns
t_{EABCLK}		0.4		0.8		1.0		1.2	ns
t_{EABCO}		0.1		0.2		0.3		0.4	ns
$t_{EABBYPASS}$		0.9		1.1		1.3		1.6	ns
t_{EABSU}	0.8		1.5		1.8		2.2		ns
t_{EABH}	0.8		1.6		2.0		2.5		ns
t_{AA}		5.5		8.2		10.0		12.4	ns
t_{WP}	6.0		4.9		6.0		7.4		ns
t_{WDSU}	0.1		0.8		1.0		1.2		ns
t_{WDH}	0.1		0.2		0.3		0.4		ns
t_{WASU}	0.1		0.4		0.5		0.6		ns
t_{WAH}	0.1		0.8		1.0		1.2		ns
t_{WO}		2.8		4.3		5.3		6.5	ns
t_{DD}		2.8		4.3		5.3		6.5	ns
t_{EABOUT}		0.5		0.4		0.5		0.6	ns
t_{EABCH}	2.0		4.0		4.0		4.0		ns
t_{EABCL}	6.0		4.9		6.0		7.4		ns

Table 102. EPF10K100A Device EAB Internal Timing Macroparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{EABAA}		6.8		7.8		9.2	ns
$t_{EABRCCOMB}$	6.8		7.8		9.2		ns
$t_{EABRCREG}$	5.4		6.2		7.4		ns
t_{EABWP}	3.2		3.7		4.4		ns
$t_{EABWCCOMB}$	3.4		3.9		4.7		ns
$t_{EABWCREG}$	9.4		10.8		12.8		ns
t_{EABDD}		6.1		6.9		8.2	ns
$t_{EABDATACO}$		2.1		2.3		2.9	ns
$t_{EABDATASU}$	3.7		4.3		5.1		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	2.8		3.3		3.8		ns
t_{EABWEH}	0.0		0.0		0.0		ns
$t_{EABWDSU}$	3.4		4.0		4.6		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	1.9		2.3		2.6		ns
t_{EABWAH}	0.0		0.0		0.0		ns
t_{EABWO}		5.1		5.7		6.9	ns

101 Innovation Drive
San Jose, CA 95134
(408) 544-7000
http://www.altera.com
Applications Hotline:
(800) 800-EPLD
Customer Marketing:
(408) 544-7104
Literature Services:
lit_req@altera.com

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